ABSTRACT

A semiconductor device includes an isolation structure having first and second sidewalls opposite each other, a first fin-shaped pattern in contact with the first sidewall and extending in the second direction, a second fin-shaped pattern in contact with the second sidewall and extending in the second direction, a first gate electrode on the first fin-shaped pattern, a first source/drain contact on the first and second fin-shaped patterns and extending between the first gate electrode and the element isolation structure, and a wiring structure on and connected to the first source/drain contact, wherein the first source/drain contact includes a lower contact intersecting the first and second fin-shaped patterns, an upper contact protruding from the lower contact, and a dummy contact, the wiring structure being in contact with the upper contact and not with the dummy contact.

FIG. 1